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(54) Title: SYSTEM AND METHOD FOR DEPOSITING INORGANIC/ORGANIC DIELECTRIC FILMS

(57) Abstract: A system and method for depositing a dielectric film on the surface of a substrate is provided having a processing chamber with a substrate support for supporting a substrate and one or more gas inlets for conveying gases to the processing chamber. A first plasma source defining a first plasma zone within the chamber is provided, and a second plasma source defining a second plasma zone within said chamber is provided. Gases are separately ionized at different ionization levels in the first and second plasma zones, and these separately ionized gases react to form a dielectric film on the surface of the substrate.

WO 01/36703 A1